	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e	r D e f	E r r o r s
1	BRS	0	non adj volatile near memory and memory near array and decoder and driver and amplifier and (trench or groove) with memory with array with (periperal or logic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/27 23:09			0
2	BRS	4	non adj volatile near memory and memory near array and decoder and driver and amplifier and (trench or groove) with memory with array with (peripheral or logic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/27 05:11			0
3	BRS	8	memory near array and decoder and driver and amplifier and (trench or groove) with memory with array with (periperal or logic)		2004/06/27 05:14			0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e	r D e f i	E r r
4	BRS	20	memory near array and decoder and driver and amplifier and (trench or groove) with memory with array with (peripheral or logic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/27 16:29			0
5	BRS		non adj volatile near memory and control near gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/27 17:44			0
6	BRS	0.0	, -	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/27 18:09			0
7	BRS	10			2004/06/27 17:48			0

	Тур	Hi ts	Search Text	DBs	Time	Stamp	m m e	ErrorDefinitio	<b>Еннон</b>
8	BRS	19	non adj volatile near memory and control near gate and (charge near stor\$6 or capacitor) near (trench or isolat\$6 or field adj (oxide or dielectric)) and control adj gate with (top or over) with (charge near storage or capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/ 19:33				0
9	BRS		non adj volatile near memory and control near gate and (charge near stor\$6 or capacitor) near (trench or isolat\$6 or field adj (oxide or dielectric)) and control adj gate with shield\$6 with (charge near storage or capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/ 18:05		-		0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e n	r D e f i	r r o r
10	BRS	1	non adj volatile near memory and control near gate with shield\$6 with (charge near stor\$6 or capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/27 21:55			0
11	BRS	1	2003-222213.NR AN.	DERWENT	2004/06/27 18:11			0
12	BRS	6	memory and control near gate with shield\$6 with (charge near stor\$6 or capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/27 18:14			0
13	IS& R	2	("6281075").PN	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/27 19:34			0
14	IS& R	2	("6406961").PN	世島野五甲身B US-PGPUB; EPO; JPO; DERWENT;	2004/06/27 19:35			0
15	IS& R	2	("6151248").PN	世島姓 <u>入</u> 平 <b>DB</b> US-PGPUB; EPO; JPO; DERWENT;	2004/06/27 19:35			0
16	BRS	4		IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/27 21:56			0
17	BRS	42			2004/06/27 21:58			0
18	IS& R	3	: 1 " 74 / 14 / 3" 1 PN i	USPAT; US-PGPUB; EPO; JPO; DERWENT; LBM TDB	2004/06/28 08:31			0

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	Тур е	Hi ts	Search Text	DBs	Time Stamp	m m e	ErrorDefinitio	r o r
19	BRS	7	5471423.URPN.	USPAT	2004/06/28 08:15			0
20	BRS	3	("4959812"   "5299162"   "5299166").PN.	USPAT	2004/06/28 08:19			0
21	IS& R	2	("6180457").PN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/28 10:28			0